New Jersey Semi-Conductor Products, Inc.

20 STERN AVE.
SPRINGFIELD, NEW JERSEY 07081
U.S.A.

TELEPHONE: (973) 376-2922
(212) 227-6005
FAX: (973) 376-8960

Rectifier Diode
Avalanche Diode

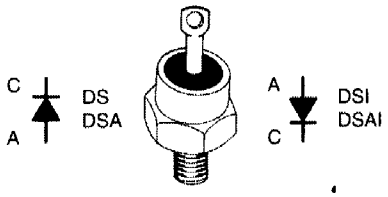
V_{RRM} = 1200-1800 V
$I_{F(RMS)}$ = 80 A
$I_{F(AV)M}$ = 49 A

V_{RSM} V	$V_{(BR)min}$ ① V	V_{RRM} V	Anode on stud	Cathode on stud
1300	-	1200	DS35-12A	DSI35-12A
1300	1300	1200	DSA35-12A	DSAI35-12A
1700	1750	1600	DSA35-16A	DSAI35-16A
1900	1950	1800	DSA35-18A	DSAI35-18A

① Only for Avalanche Diodes

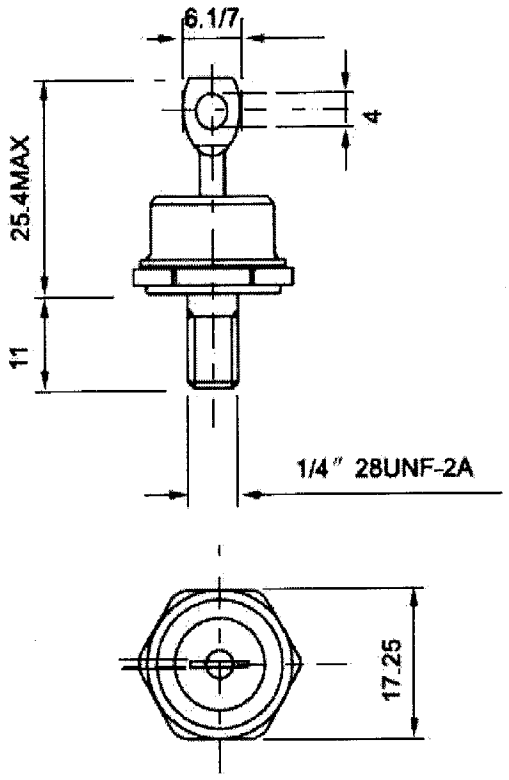
Symbol	Test Conditions		Maximum Ratings	
$I_{F(RMS)}$ $I_{F(AVM)}$	$T_{VJ} = T_{VJM}$ T_{case} = 100°C; 180° sine		80 49	A A
P_{RSM}	DSA(I) types, $T_{VJ} = T_{VJM}$, t_p = 10 µs		11	kW
I_{FSM}	T_{VJ} = 45°C;	t = 10 ms (50 Hz), sine	650	A
	V_R = 0	t = 8.3 ms (60 Hz), sine	690	A
	$T_{VJ} = T_{VJM}$	t = 10 ms (50 Hz), sine	600	A
	V_R = 0	t = 8.3 ms (60 Hz), sine	640	A
I^2t	T_{VJ} = 45°C	t = 10 ms (50 Hz), sine	2100	A^2s
	V_R = 0	t = 8.3 ms (60 Hz), sine	2000	A^2s
	$T_{VJ} = T_{VJM}$	t = 10 ms (50 Hz), sine	1800	A^2s
	V_R = 0	t = 8.3 ms (60 Hz), sine	1700	A^2s
T_{VJ}			-40...+180	°C
T_{VJM}			180	°C
T_{stg}			-40...+180	°C
M_d	Mounting torque		4.5-5.5	Nm
			40-49	lb.in.
Weight			15	g

Symbol	Test Conditions	Characteristic Values		
I_R	$T_{VJ} = T_{VJM}$; $V_R = V_{RRM}$	≤	4	mA
V_F	I_F = 150 A; T_{VJ} = 25°C	≤	1.55	V
V_{T0}	For power-loss calculations only		0.85	V
r_T	$T_{VJ} = T_{VJM}$		4.5	mΩ
R_{thJC}	DC current		1.05	K/W
R_{thJH}	DC current		1.25	K/W
d_S	Creepage distance on surface		4.05	mm
d_A	Strike distance through air		3.9	mm
a	Max. allowable acceleration		100	m/s^2



A = Anode C = Cathode

Quality Semi-Conductors



For metric devices:M6×1

DO-5